E lectron-hole asym m etry in m agnetic properties of lightly doped high- $T_{\rm C}$ superconductors: a quantum M onte C arlo study

Seiji Yunoki and Sandro Sorella^y
International School for Advanced Studies (SISSA), via Beirut 4, 34014 Trieste, Italy

Using a recently developed variational quantum M onte Carlo method, magnetic properties of high- $T_{\rm C}$ superconductors are studied at zero temperature (T), by numerical simulations on the 2D t-J model. Our focus here is to explore the dierence in the properties of p-type and n-type cuprates as a function of the carrier concentrations close to half lling. As observed experimentally, it is found that the antiferrom agnetically ordered phase persists even for a small, yet nite amount of carrier doping, and that this phase is more robust in the electron doped case.

There have been stimulating studies on high- $T_{\rm C}$ superconductors to explore the underlying mechanism and unusual normal state properties. Experimentally much attention has been recently devoted to rather lightly doped p-and n-type cuprates [1]. This is partially because high quality samples have become now available, and because it is now clear that understanding the evolution of the electronic state with carrier doping from undoped M ott insulator is crucial to clarify the nature of the systems. Theoretically it is still in the middle of extensive debate. It is widely accepted however that a 2D t-J-like model can describe low-energy physics of cuprates de ned by the following H am iltonian [2];

Here the notation is conventional (see e.g., Ref [3]). Introduction of next nearest-neighbor hopping t⁰ deserves som e explanation; sm all cluster calculations have shown that the t-J model indeed capture low energy physics of more involved multi-band models with t^0 =t negative (positive) for hole-doped (electron-doped) case, at least for small carrier densities x [4]. We rem ind that this sign di erence originates from the fact that the parent cuprates are charge transfer insulators, and therefore a \carrier" represents in the model a Zhang-Rice singlet (an inert Cu d¹⁰ con guration) for the hole (electron) doped system. It is also now widely accepted that, in the half-lling undoped case, the model shows antiferrom agnetic (AFM) long-range order at T = 0. It is very interesting therefore to study theoretically how strong this AFM phase is against carrier doping and how the robustness of the phase depends on the nature of doped carriers.

There exist several num erical studies on small clusters (26 sites) indicating that at nite x close to half-lling positive (negative) t^0 =tenhances (degrades) AFM correlations compared to t^0 =0 [5]. Although these results might give the correct trend at short distances, it is difcult within such small cluster calculations to really as-

sess the existence of long-range order. For this purpose we have studied this issue using quantum M onte Carlo techniques, which allows much larger sizes (' 100 sites).

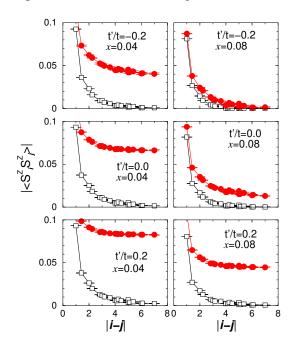


FIG. 1: A bsolute value of real-space spin correlation functions for 2D t-t $^{\circ}$ -J m odel with J=t= 0.3 and t $^{\circ}$ -t= 0.2 (top), 0.0 (m iddle), and 0.2 (bottom). Carrier densities x are 0.04 (left) and 0.08 (right) on a tilted square lattice of 98 98.0 pen squares and solid circles are for VMC and FN, respectively.

To study ground sate properties of the 2D tt⁰-J m odel (1), we employ a recently developed variational quantum M onte C arlo m ethod by Sorella $[\beta, 6]$. Results presented here are computed by variational and xed node m ethods (VMC and FN, respectively), and the details on how to m inim ize the energy for a variational wave function with m any parameters are found in Ref. $[\beta]$. We just mention here that we employ the most general singlet variational wave function of the Jastrow-BCS form, with a pairing function of d-wave symmetry. The Jastrow factor, which includes the Gutzwiller projector, makes the wave function of the RVB type. A fiter all the possible variational

param eters are optim ized, we obtain a fairly good guiding function that is used for FN . A lso note that the variational energy of FN is lower than the one of VM C [6].

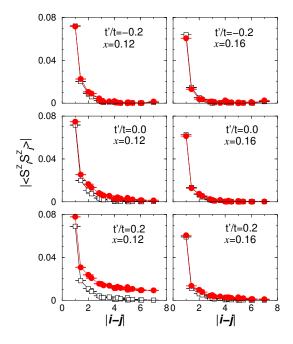


FIG .2: Same as in Fig. 1, but x = 0.12 (left) and 0.16 (right).

M ain results are summarized in Figs. 1 and 2 where real-space spin-spin correlation functions are given for various t^0 =t and doped carrier concentrations x [7] at J=t = 0:3. These results provide clear evidence that strong spin correlations remain nite at the largest distances for nite carrier concentrations x. The critical x_c above which long range order disappears apparently depends on the parameters used; for the present set of t^0 =t = 0.2,0, and 0.2, x_c ' 0.06,0.08, and 0.12, respectively. Of particular interest is the result that the spin

correlations are enhanced (degraded) when positive (negative) t^0 =t is incorporated into the model, corresponding to electron (hole) doing. Our results are consistent with the previous studies [5, 8] and experimental observations [9].

In conclusion, magnetic properties of the lightly doped 2D t-J model with next nearest neighbor hopping t^0 are numerically studied to understand the dierent behaviors as a function of carrier concentrations for hole (t^0 =t<0) and electron (t^0 =t>0) doping. Our large cluster calculations clearly show that AFM long-range order exists away from half-lling and is more robust for the electron doped case. These results compare very well with experimental observations. More detailed analyses and other properties will be presented in a separate paper [10].

This work was supported by M IUR-COFIN 2001.

- E lectronic address: yunoki@ sissa.it
- ^y E lectronic address: sorella@ sissa.it
- [1] S. Wakimoto, et al., Phys. Rev. B 61 (2000) 3699; N. Harima, et al., ibid. 64 (2001) 220507; Y. Ando, et al., Phys. Rev. Lett. 87 (2001) 017001; N. P. Armitage, et al., cond-mat/0201119; T. Yoshida, et al., cond-mat/0206469.
- [2] F.C. Zhang, T.M. Rice, Phys. Rev. B 37 (1988) 3759.
- [3] S. Sorella, ibid. 64 (2001) 024512; cond-m at/0201388.
- [4] H. Eskes, et al., Physica C 160 (1989) 424; T. Tohyam a, et al., J. Phys. Soc. Jpn. 59 (1990) 1760.
- [5] T. Tohyam a, et al., Phys. Rev. B 49 (1994) 3596; R.
 J. Gooding, et al., ibid. 50 (1994) 12866; see also G.B.
 Martins, et al., ibid. 64 (2001) 180513; T. Tohyam a, et al., ibid. 64 (2001) 212505.
- [6] See also D.F.B.ten Haaf, et al., ibid. 51 (1995) 13039.
- [7] Note that x = 0 corresponds to undoped system s.
- [8] See also S. Sorella, et al., Phys. Rev. Lett. 88 (2002) 117002.
- [9] See, e.g., M. M atsuda, et al., Phys. Rev. B 62 (2000) 9148; M. Fu jita, et al., cond-m at/0203320.
- [10] S. Yunoki, S. Sorella, preprint.